

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

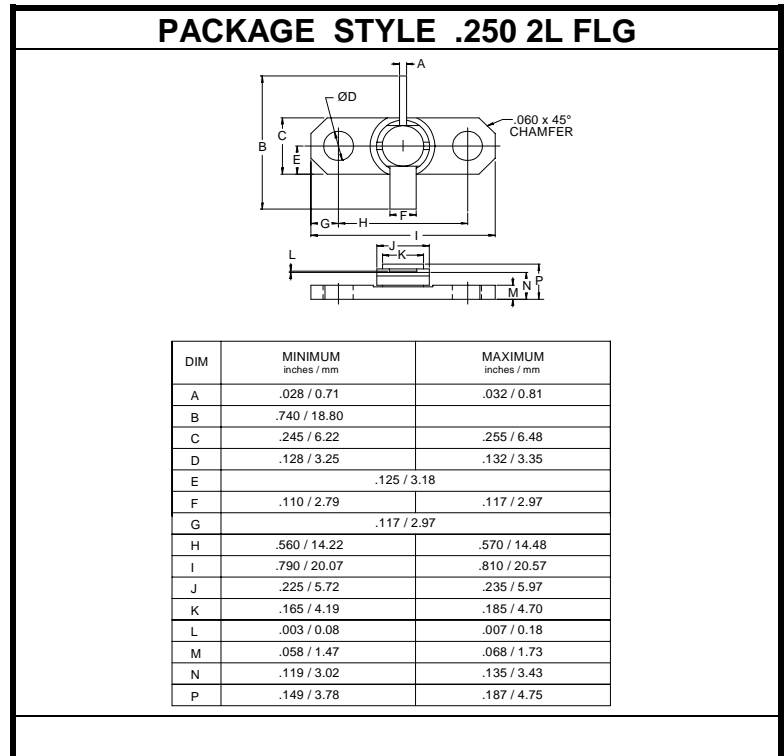
The **ASI TH9030** is Designed for General Purpose Power oscillator Amplifier Applications up to 2.3 GHz.

FEATURES:

- Common Collector
- Hermetic Microstrip Package
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	600 mA
V_{CEO}	20 V
V_{CBO}	45 V
V_{EBO}	3.0 V
P_{DISS}	7.0 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	25 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CBO}	V _{CB} = 30 V					.25	mA
I_{EBO}	V _{EB} = 2.0 V					.25	mA
h_{FE}	V _{CE} = 5.0 V	I _C = 100 mA		15		120	---
C_{OB}	V _{CB} = 20 V	f = 1.0 MHz			1.5	2.5	pF
P_{osc}	V _{CE} = 18 V	I _E = 250 mA	f = 2.3 GHz		1.6		W